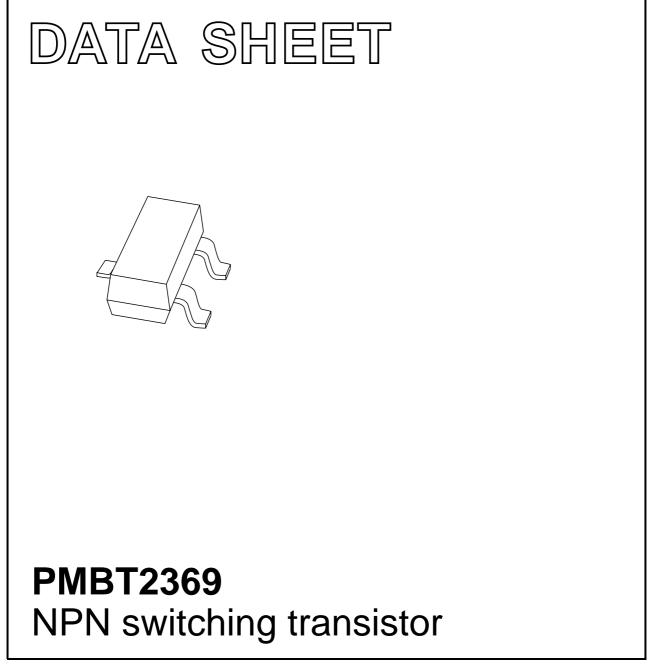
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 Apr 27 2004 Jan 22



Product data sheet

PMBT2369

NPN switching transistor

FEATURES

- Low current (max. 200 mA)
- Low voltage (max. 15 V).

APPLICATIONS

• High-speed switching, especially in portable equipment.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾		
PMBT2369	*1J		

Note

- 1. * = p : Made in Hong Kong.
- * = t : Made in Malaysia.

* = W : Made in China.

ORDERING INFORMATION

TYPE		PACKAGE		
NUMBER	NAME	DESCRIPTION	VERSION	
PMBT2369	_	plastic surface mounted package; 3 leads	SOT23	

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V _{CEO}	collector-emitter voltage	open base	-	15	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current (DC)		_	200	mA
I _{CM}	peak collector current		-	300	mA
I _{BM}	peak base current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	

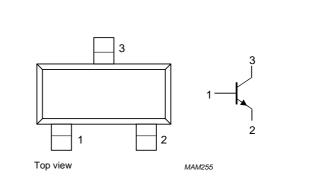


Fig.1 Simplified outline (SOT23) and symbol.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

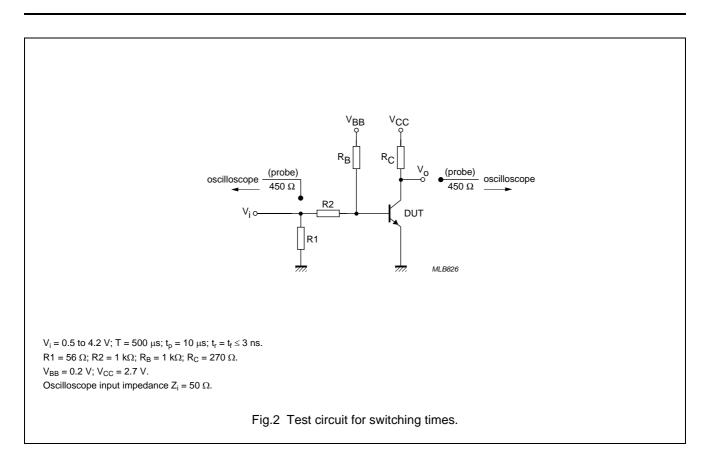
1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

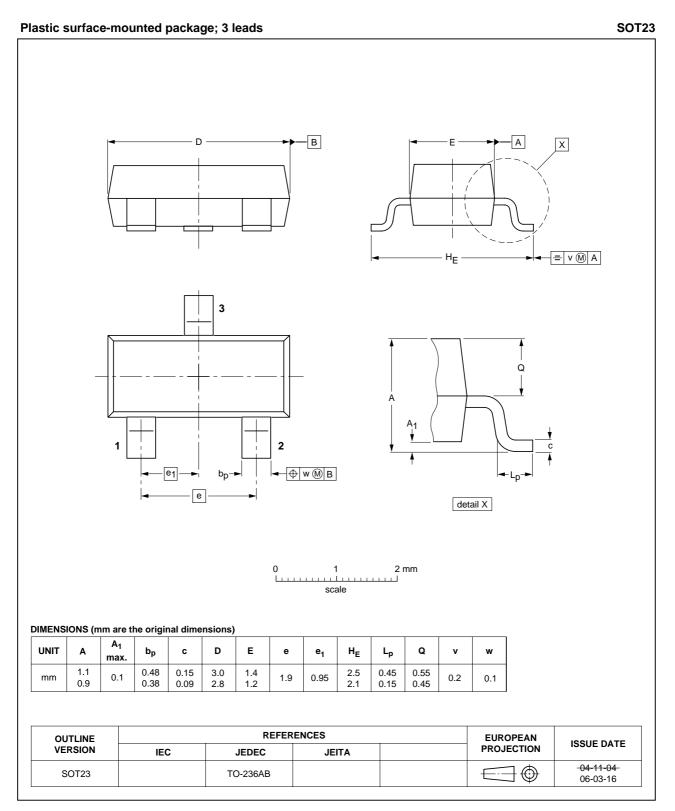
 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 20 V	_	400	nA
		I _E = 0; V _{CB} = 20 V; T _j = 125 °C	_	30	μA
I _{EBO}	emitter cut-off current	$I_{C} = 0; V_{EB} = 4 V$	_	100	nA
h _{FE}	DC current gain	I _C = 10 mA; V _{CE} = 1 V	40	120	
		I_{C} = 10 mA; V_{CE} = 1 V; T_{amb} = -55 °C	20	_	
		I _C = 100 mA; V _{CE} = 2 V	20	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	_	250	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	700	850	mV
Cc	collector capacitance	$I_E = I_e = 0; V_{CB} = 5 V; f = 1 MHz$	-	4	pF
f _T	transition frequency	I _C = 10 mA; V _{CE} = 10 V; f = 100 MHz	500	-	MHz
Switching t	imes (between 10% and 90% levels)); (see Fig.2)			
t _{on}	turn-on time	I _{Con} = 10 mA; I _{Bon} = 3 mA;	_	10	ns
t _d	delay time	I _{Boff} = –1.5 mA	_	4	ns
t _r	rise time		_	6	ns
t _{off}	turn-off time]	-	20	ns
ts	storage time	1	_	10	ns
t _f	fall time	1	_	10	ns

PMBT2369



PACKAGE OUTLINE



PMBT2369

PMBT2369

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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Printed in The Netherlands

R75/04/pp7

Date of release: 2004 Jan 22

Document order number: 9397 750 12458

